

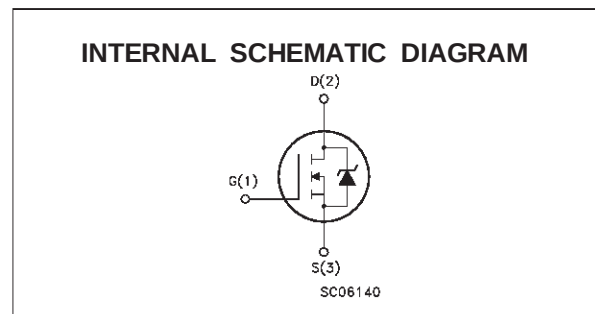
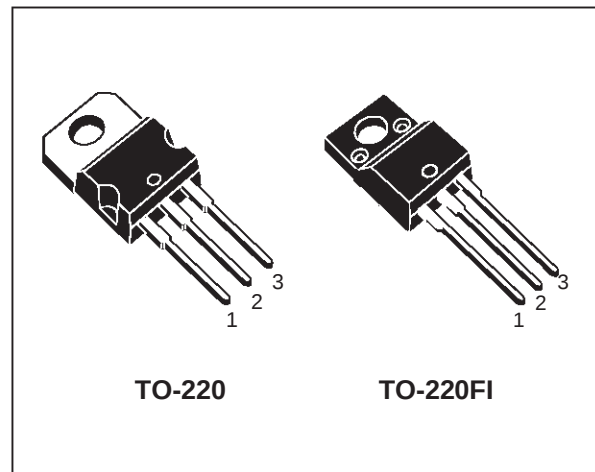
N - CHANNEL 100V - 0.050Ω - 30A - TO-220/TO-220FI POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
IRF540	100 V	< 0.077 Ω	30 A
IRF540FI	100 V	< 0.077 Ω	16 A

- TYPICAL R_{DS(on)} = 0.050 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175°C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- DC-DC & DC-AC CONVERTER
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMP DRIVERS Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		IRF530	IRF530FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 kΩ)	100		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	30	17	A
I _D	Drain Current (continuous) at T _c = 100 °C	21	12	A
I _{DM} (●)	Drain Current (pulsed)	120	120	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	45	W
	Derating Factor	1	0.3	W/°C
V _{iso}	Insulation Withstand Voltage (DC)	-	2000	V
T _{stg}	Storage Temperature	-65 to 175		°C
T _j	Max. Operating Junction Temperature	175		°C

(●) Pulse width limited by safe operating area

(1) I_{SD} ≤ 30 A, di/dt ≤ 200 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}

THERMAL DATA

		TO-220	TO220-FI	
$R_{thj-case}$	Thermal Resistance Junction-case	Max	1	3.33
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	62.5	$^{\circ}C/W$
$R_{thc-sink}$	Thermal Resistance Case-sink	Typ	0.5	$^{\circ}C/W$
T_l	Maximum Lead Temperature For Soldering Purpose		300	$^{\circ}C$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	30	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^{\circ}C$, $I_D = I_{AR}$, $V_{DD} = 25 V$)	200	mJ

ELECTRICAL CHARACTERISTICS ($T_{case} = 25^{\circ}C$ unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 250 \mu A$ $V_{GS} = 0$	100			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$ $T_c = 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ $I_D = 250 \mu A$	2	3	4	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V$ $I_D = 15 A$		0.05	0.077	Ω
$I_{D(on)}$	On State Drain Current	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $V_{GS} = 10 V$	30			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (*)$	Forward Transconductance	$V_{DS} > I_{D(on)} \times R_{DS(on)max}$ $I_D = 15 A$	10	20		S
C_{iss}	Input Capacitance	$V_{DS} = 25 V$ $f = 1 MHz$ $V_{GS} = 0$		2600	3600	pF
C_{oss}	Output Capacitance			350	500	pF
C_{rss}	Reverse Transfer Capacitance			85	120	pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 50\text{ V}$ $I_D = 15\text{ A}$		20	28	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		60	85	ns
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$ $I_D = 30\text{ A}$ $V_{GS} = 10\text{ V}$		80	110	nC
Q_{gs}	Gate-Source Charge			13		nC
Q_{gd}	Gate-Drain Charge			28		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(V_{off})}$	Off-voltage Rise Time	$V_{DD} = 80\text{ V}$ $I_D = 30\text{ A}$		22	30	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		25	35	ns
t_c	Cross-over Time			55	75	ns

SOURCE DRAIN DIODE

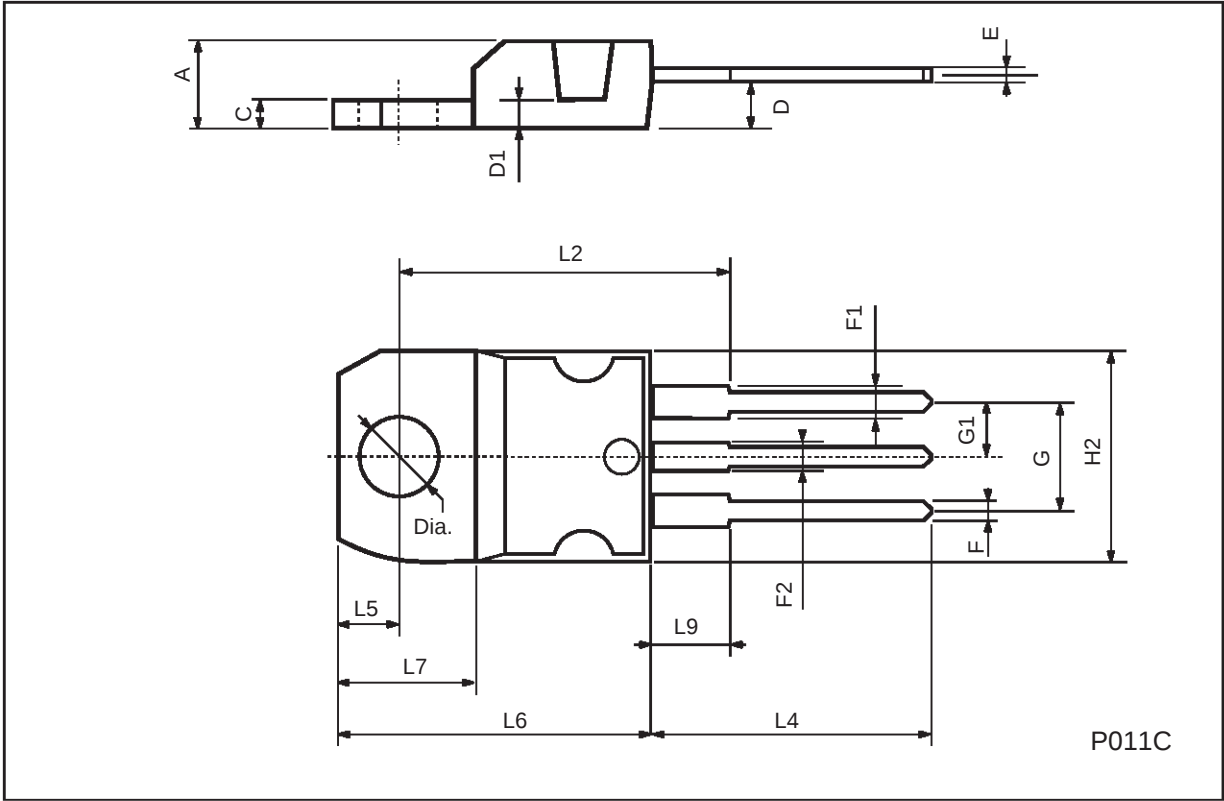
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				30	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				120	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 50\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 30\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_j = 150\text{ }^\circ\text{C}$		175		ns
Q_{rr}	Reverse Recovery Charge			1.1		μC
I_{RRM}	Reverse Recovery Current			12.5		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

($\bullet$) Pulse width limited by safe operating area

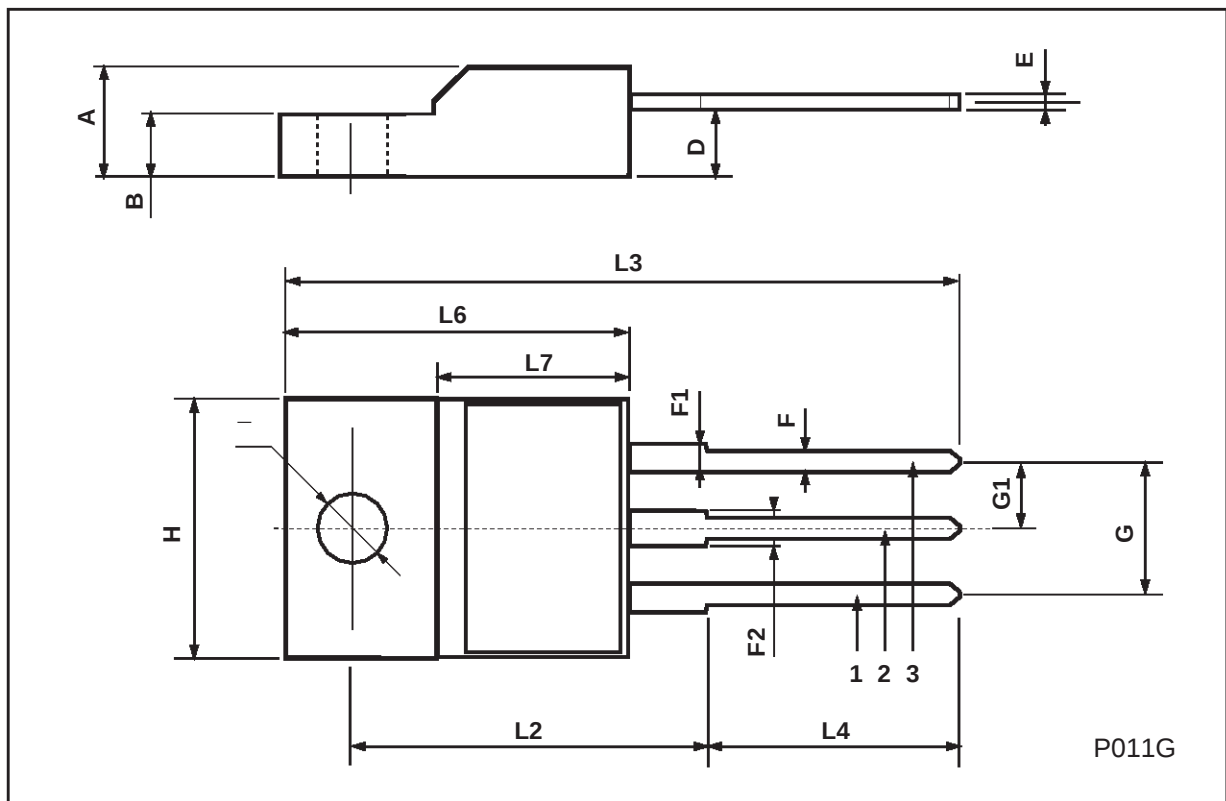
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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